

Product Introduction

Our InSb (Indium Antimonide) wafers are grown using the Vertical Gradient Freeze (VGF) method, available in 2" and 3" diameters with <100> orientation. Offered in undoped and doped variants (N-type: S,Sn; P-type: Zn), these epi-ready wafers feature tightly controlled TTV ($\leq 15\mu\text{m}$), bow ($\leq 15\mu\text{m}$), and warp ($\leq 15\mu\text{m}$) for consistent downstream processing. With polished or etched surface finishes, our InSb wafers are well suited for infrared detection and sensing applications.

Applications

- Infrared detectors and focal plane arrays
- Hall effect sensors and magnetoresistive devices
- Thermal imaging systems
- High-speed, low-power electronic devices

INDIUM ANTIMONIDE (INSB) WAFER SPECIFICATIONS		
GROWTH METHOD	VGF	
Type/Dopant	Undoped // N/S/Sn // P/Zn	
Diameter(mm)	50.8 $\pm$ 0.3	76.2 $\pm$ 0.3
Thickness(um)	500 $\pm$ 25	650 $\pm$ 25
OF(mm)	16 $\pm$ 2	22 $\pm$ 2
IF(mm)	8 $\pm$ 2	12 $\pm$ 2
Orientation	<100>	
TTV(um)	≤ 10	≤ 15
Bow(um)	≤ 15	≤ 15
Wrap(um)	≤ 15	≤ 15
Surface	Polished/Etched	
Epi-ready	Yes	